

HSKT570 Thyristor Modules



Features:

- Isolated mounting base 2500V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

Typical Applications

- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

V_{DSM}, V_{RSM}	V_{DRM}, V_{RRM}	Type & Outline		
900V 1100V	800V 1000V	HSKT570-08-416F3 HSKT570-10-416F3		
1300V	1200V	HSKT570-12-416F3		
1500V 1700V	1400V 1600V	HSKT570-14-416F3 HSKT570-16-416F3		
1900V	1800V	HSKT570-18-416F3		

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	- 40.53	VALUE					
			T _j (°C)	Min	Туре	Max	UNIT		
I _{T(AV)}	Mean on-state current	180° half sine wave 50Hz Single side cooled,T _c =85°C	125			570	Α		
I _{T(RMS)}	RMS on-state current					895	Α		
I _{DRM} I _{RRM}	Repetitive peak current	at V _{DRM} at V _{RRM}	125			35	mA		
I _{TSM}	Surge on-state current	10ms half sine wave	125			15	kA		
l²t	I ² t for fusing coordination	$V_R=60\%V_{RRM}$				1125	A ² s*10 ³		
V _{TO}	Threshold voltage		125			0.80	V		
r _T	On-state slope resistance					0.20	mΩ		
V _{TM}	Peak on-state voltage	I _{TM} =1600A	25			1.45	V		
dv/dt	Critical rate of rise of off-state voltage	V _{DM} =67%V _{DRM}	125			800	V/µs		
di/dt	Critical rate of rise of on-state current	Gate source 1.5A t _r ≤0.5µs Repetitive	125			100	A/µs		
I _{GT}	Gate trigger current	V _A =12V, I _A =1A		30		200	mA		
V _{GT}	Gate trigger voltage		25	1.0		3.0	V		
I _H	Holding current			20		200	mA		
V_{GD}	Non-trigger gate voltage	V_{DM} =67% V_{DRM}	125	0.2			V		
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled per chip				0.065	°C /W		
$R_{\text{th(c-h)}}$	Thermal resistance case to heatsink	Single side cooled per chip				0.024	°C /W		
V _{iso}	Isolation voltage	50Hz,R.M.S,t=1min,I _{iso} :1mA(MAX)		2500			V		
_	Terminal connection torque(M10)				12.0		N·m		
F _m	Mounting torque(M6)				6.0		N·m		
T _{vj}	Junction temperature			-40		125	°C		
T_{stg}	Stored temperature			-40		125	°C		
W _t	Weight				1500		g		
Outline	416F3								



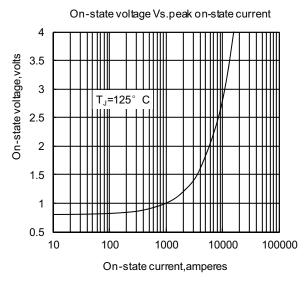


Fig1

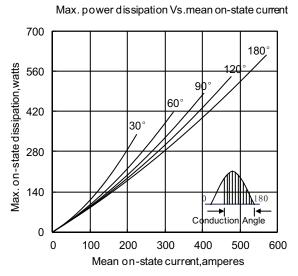
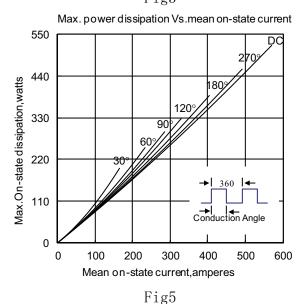


Fig3



Max. junction to case thermal impedance Vs.time

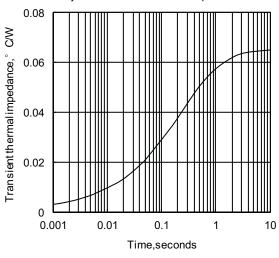


Fig2

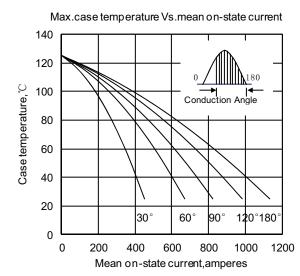


Fig4

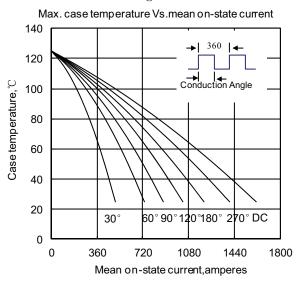
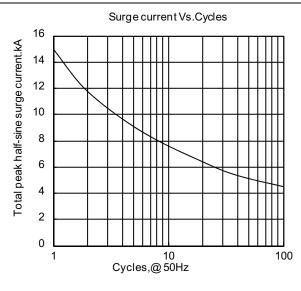


Fig6







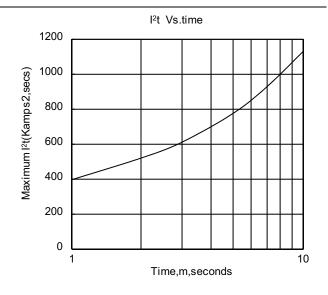
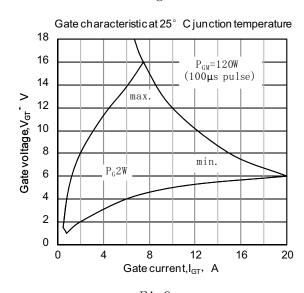
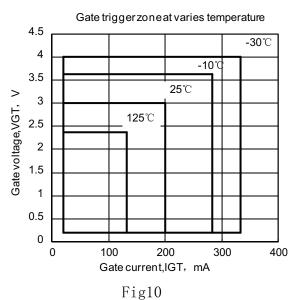
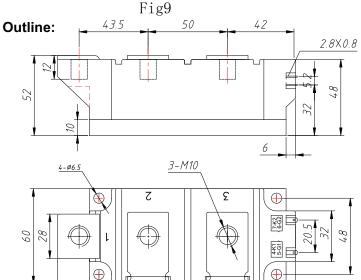


Fig7









112 124 150

